

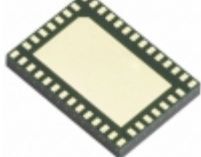
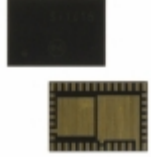


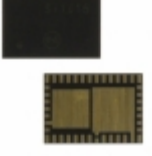


	<h2>SI1013X-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI1013X-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 350MA SC89-3</p> <p>Datenblätter:  SI1013X-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 103166 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1013X-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 350MA SC89-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	103166 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	P-Channel 20V 350mA (Ta) 250mW (Ta) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SC-89, SOT-490
Supplier Device-Gehäuse	SC-89-3
Verlustleistung (max)	250mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	350mA (Ta)
Rds On (Max) @ Id, Vgs	1.2 Ohm @ 350mA, 4.5V
VGS (th) (Max) @ Id	450mV @ 250µA (Min)
Gate Charge (Qg) (Max) @ Vgs	1.5nC @ 4.5V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±6V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1013X-T1-GE3TR

SI1013X-T1-GE3 ist neu im Original, Suche SI1013X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1013X-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1013X-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1013X-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 350MA SC89-3</p>	 <p>SI1014-C-GM2R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1014-C-GM2 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1013X VISHAY SI1013X VISHAY</p>
 <p>SI1013X-T1 VISHAY SI1013X-T1 VISHAY</p>	 <p>SI1014-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-WFQFN</p>	 <p>SI1013X-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 350MA SC89-3</p>	 <p>SI1013X-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 350MA SC89-3</p>

heiße Teile

Mehr

SI1003-C-GM	SI1011X-T1-GE3	SI1011X-T1-GE3	SI1012CR-T1-GE3	SI1012CR-T1-GE3
SI1012R-T1	SI1012R-T1-E3	SI1012R-T1-E3	SI1012R-T1-GE3	SI1012R-T1-GE3
SI1012X-T1	SI1012X-T1-E3	SI1012X-T1-E3	SI1012X-T1-GE3	SI1012X-T1-GE3
SI1013CX-T1-GE3	SI1013CX-T1-GE3	SI1013R-T1	SI1013R-T1-E3	SI1013R-T1-E3
SI1013R-T1-GE3	SI1013R-T1-GE3	SI1013X-T1	SI1013X-T1-E3	SI1013X-T1-E3
SI1013X-T1-GE3	SI1016CX-T1-GE3	SI1016CX-T1-GE3	SI1016X-T1-E3	SI1016X-T1-E3
SI1016X-T1-GE3	SI1016X-T1-GE3	SI1016X2-T1-GE3	SI1021R-T1	SI1021R-T1-E3
SI1021R-T1-E3	SI1022R-T1	SI1022R-T1-E3	SI1022R-T1-E3	SI1022R-T1-GE3
SI1022R-T1-GE3	SI1022R-T1-E3	SI1023CX-T1-GE3	SI1023CX-T1-GE3	SI1023X-T1
SI1023X-T1-E3	SI1023X-T1-E3	SI1023X-T1-GE3	SI1023X-T1-GE3	SI1024-T1

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